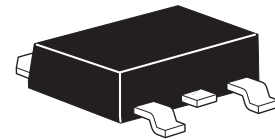


# ZXMN10A11K

## 100V DPAK N-channel enhancement mode MOSFET

### Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
100	0.350 @ $V_{GS} = 10V$	3.5
	0.450 @ $V_{GS} = 6V$	3.1



### Description

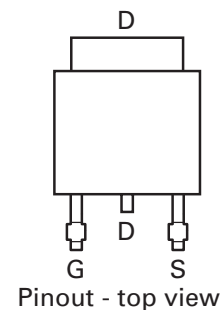
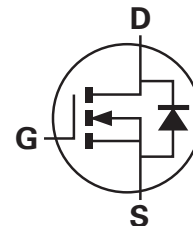
This new generation trench MOSFET from Zetex features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

### Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- DPAK package

### Applications

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control



### Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A11KTC	13	16	2,500

### Device marking

ZXMN  
10A11

# ZXMN10A11K

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	$V_{DSS}$	100	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current @ $V_{GS} = 10V$ ; $T_{amb} = 25^{\circ}C^{(b)}$ @ $V_{GS} = 10V$ ; $T_{amb} = 70^{\circ}C^{(b)}$ @ $V_{GS} = 10V$ ; $T_{amb} = 25^{\circ}C^{(a)}$	$I_D$	3.5 2.8 2.4	A
Pulsed drain current <sup>(c)</sup>	$I_{DM}$	9.9	A
Continuous source current (body diode) <sup>(b)</sup>	$I_S$	8.35	A
Pulsed source current (body diode) <sup>(c)</sup>	$I_{SM}$	9.9	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$ Linear derating factor	$P_D$	4.06 32.4	W mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$ Linear derating factor	$P_D$	8.5 68	W mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$ Linear derating factor	$P_D$	2.11 16.8	W mW/°C
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150	°C

## Thermal resistance

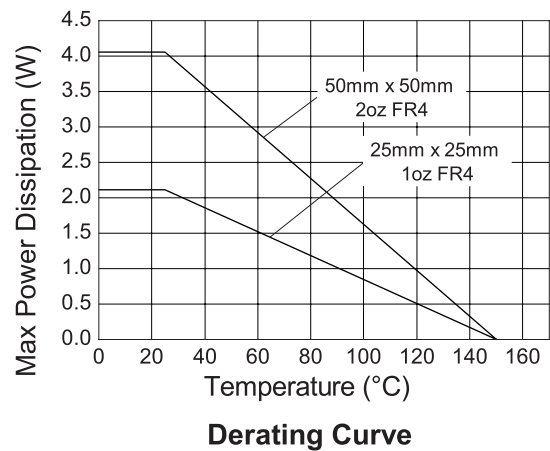
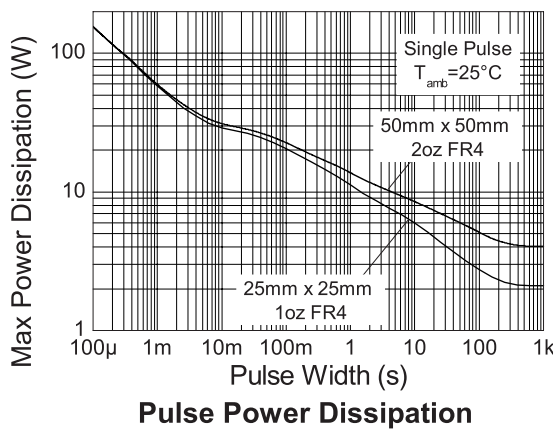
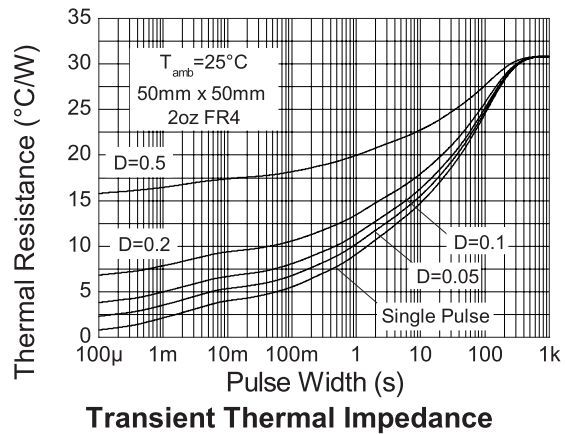
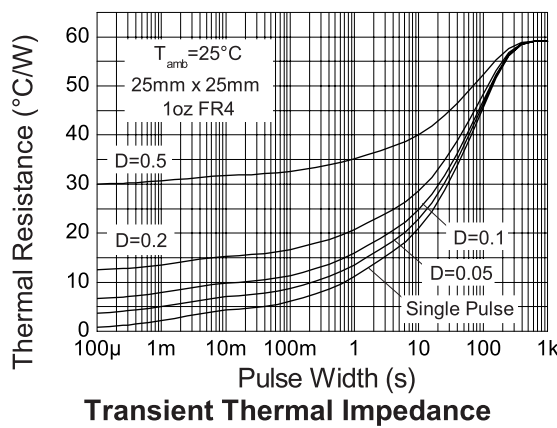
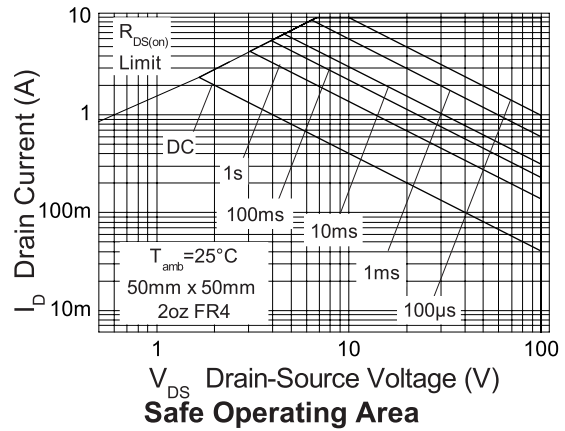
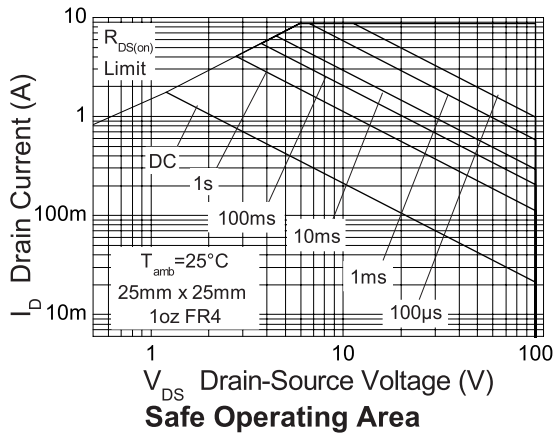
Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	30.8	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\theta JA}$	14.7	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\theta JA}$	59.1	°C/W

### NOTES:

- (a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- (b) For a device surface mounted on FR4 PCB measured at  $t \leq 10$  sec.
- (c) Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB,  $D=0.02$  pulse width=300 $\mu$ s - pulse width limited by maximum junction temperature.
- (d) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

# ZXMN10A11K

## Thermal characteristics



# ZXMN10A11K

## Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
<b>Static</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	100			V	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$
Zero gate voltage drain current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS} = 100\text{V}$ , $V_{GS} = 0\text{V}$
Gate-body leakage	$I_{GSS}$			100	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
Gate-source threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$I_D = 250\mu\text{A}$ , $V_{DS} = V_{GS}$
Static drain-source on-state resistance (*)	$R_{DS(on)}$			0.350	$\Omega$	$V_{GS} = 10\text{V}$ , $I_D = 2.6\text{A}$
				0.450	$\Omega$	$V_{GS} = 6\text{V}$ , $I_D = 1.3\text{A}$
Forward transconductance(*) (‡)	$g_{fs}$		4		S	$V_{DS} = 15\text{V}$ , $I_D = 2.6\text{A}$
<b>Dynamic</b> (‡)						
Input capacitance	$C_{iss}$		274		pF	$V_{DS} = 50\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output capacitance	$C_{oss}$		21		pF	
Reverse transfer capacitance	$C_{rss}$		11		pF	
<b>Switching</b> (†) (‡)						
Turn-on-delay time	$t_{d(on)}$		2.7		ns	$V_{DD} = 50\text{V}$ , $I_D = 1\text{A}$ $R_G \approx 6.0\Omega$ , $V_{GS} = 10\text{V}$
Rise time	$t_r$		1.7		ns	
Turn-off delay time	$t_{d(off)}$		7.4		ns	
Fall time	$t_f$		3.5		ns	
Gate charge	$Q_g$		3		nC	$V_{DS} = 50\text{V}$ , $V_{GS} = 5\text{V}$ $I_D = 2.5\text{A}$
Total gate charge	$Q_g$		5.4		nC	$V_{DS} = 50\text{V}$ , $V_{GS} = 10\text{V}$ $I_D = 2.5\text{A}$
Gate-source charge	$Q_{gs}$		1.4		nC	
Gate drain charge	$Q_{gd}$		1.5		nC	
<b>Source-drain diode</b>						
Diode forward voltage(*)	$V_{SD}$		0.85	0.95	V	$T_j = 25^{\circ}\text{C}$ , $I_S = 1.85\text{A}$ , $V_{GS} = 0\text{V}$
Reverse recovery time (‡)	$t_{rr}$		26		ns	$T_j = 25^{\circ}\text{C}$ , $I_S = 1\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge (‡)	$Q_{rr}$		30		nC	

### NOTES:

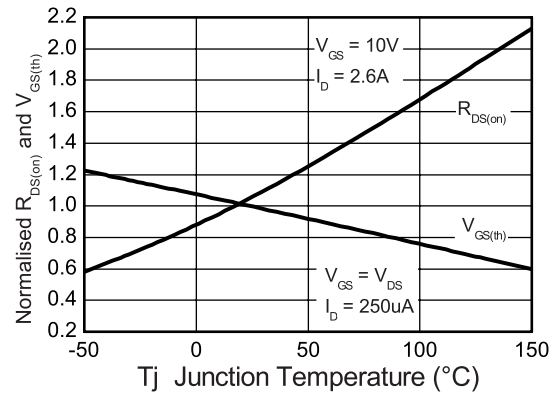
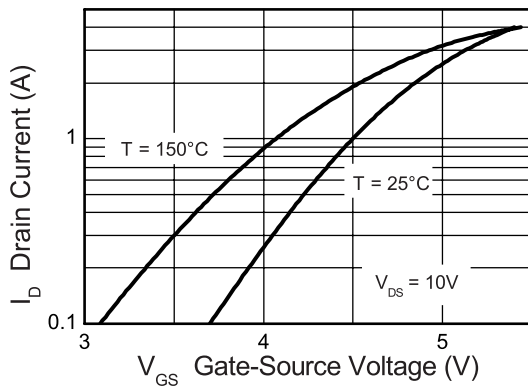
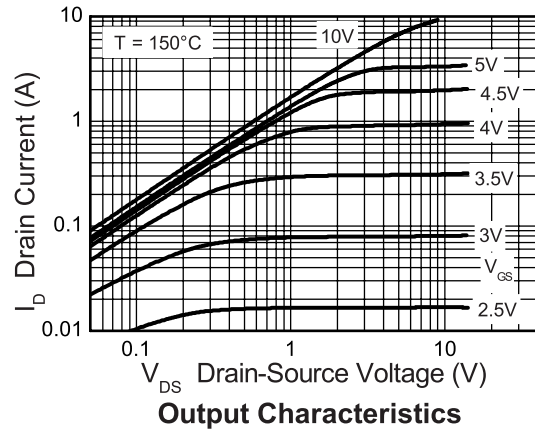
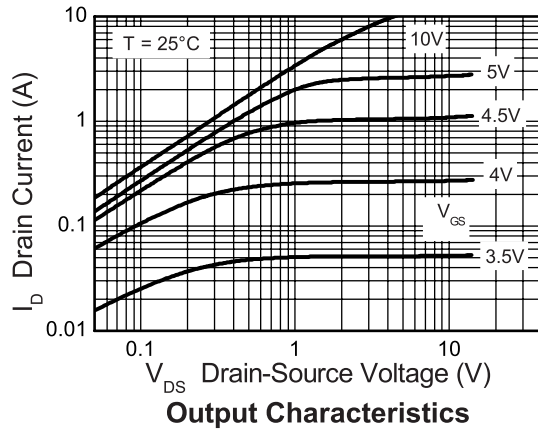
(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing.

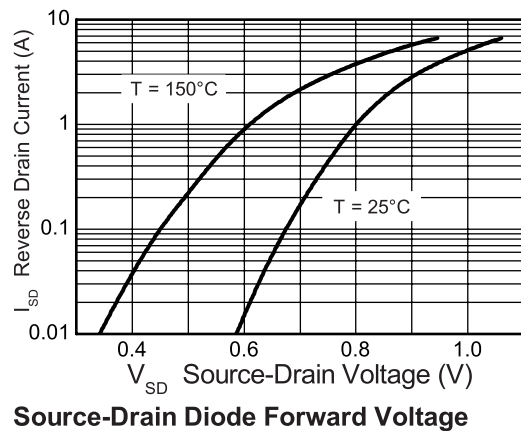
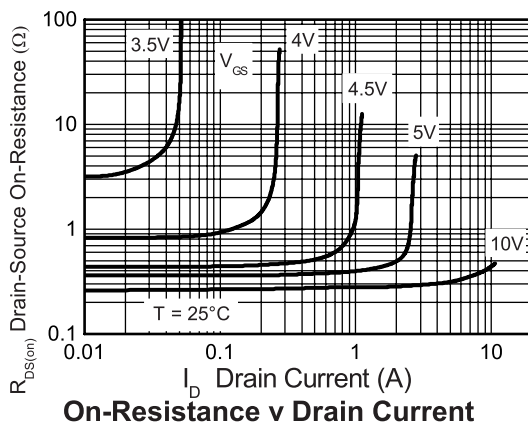
# ZXMN10A11K

## Typical Characteristics



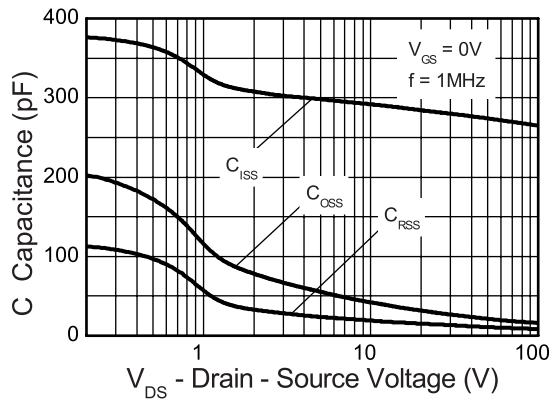
## Typical Transfer Characteristics

## Normalised Curves v Temperature

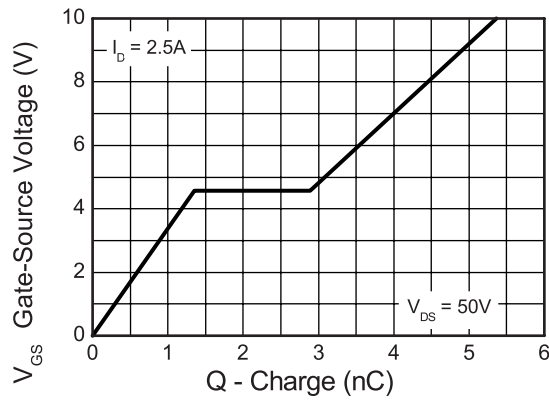


# ZXMN10A11K

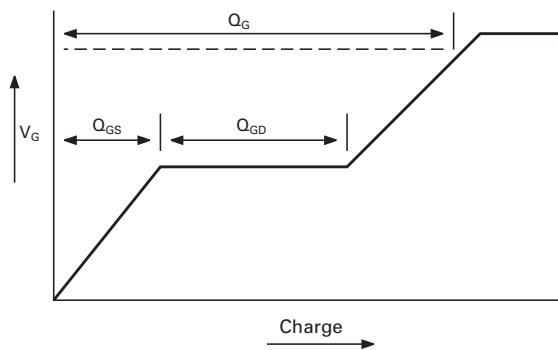
## Typical Characteristics



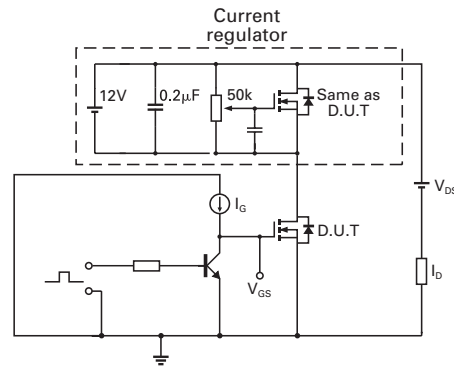
Capacitance v Drain-Source Voltage



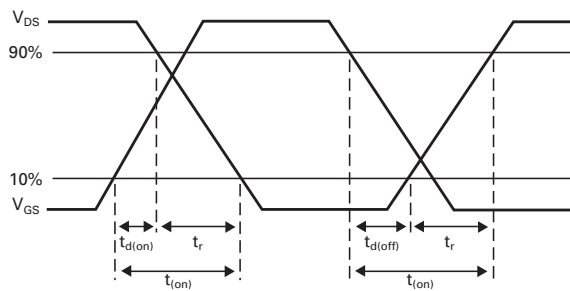
Gate-Source Voltage v Gate Charge



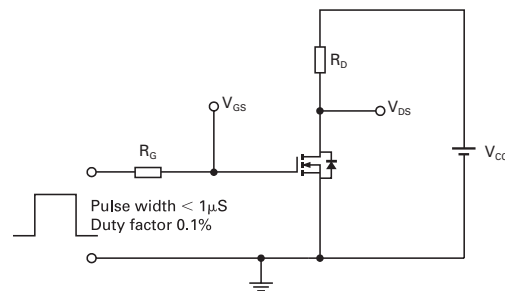
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



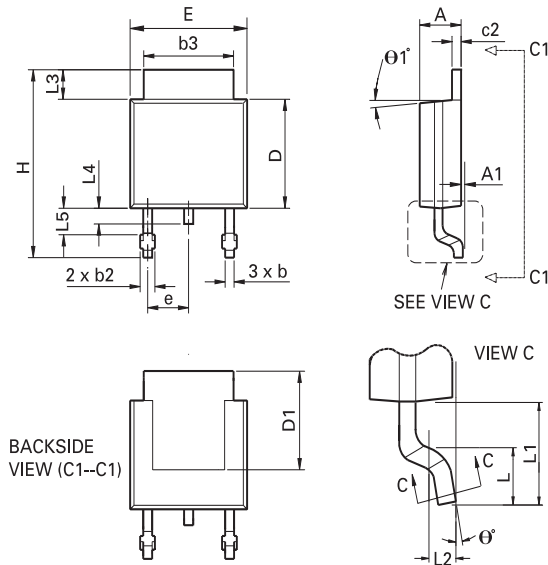
Switching time test circuit

# ZXMN10A11K

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# ZXMN10A11K

## Package outline - DPAK



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	theta 1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	theta 0°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

**Note:** Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

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